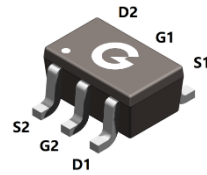
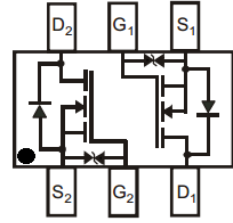


Features

- Low on-resistance
- High-speed switching
- Drive circuits can be simple
- Parallel use is easy
- HBM: AEC-Q101-001: H2 (JESD22-A114-B: 2)
- Halogen free
- Qualified to AEC-Q101 standards for high reliability

HF



SOT-363

Typical Applications

- N-channel enhancement mode effect transistor
- Switching application

Mechanical Data

- Case: SOT-363
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin-Plated Leads, Solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TBSS7002DW	SOT-363	3000 pcs / Tape & Reel	K7D

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate -Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (T _A = 25°C) *1	I _D	300	mA
Continuous Drain Current (T _A = 70°C) *1		240	mA
Pulsed Drain Current (t _p = 10μs, T _A = 25°C)	I _{DM}	2000	mA
Single Pulse Avalanche Energy *3	E _{AS}	0.11	mJ
Power Dissipation (T _A = 25°C) *1	P _D	0.34	W
Operating Junction Temperature Range	T _J	-55 ~ +150	°C
Storage Temperature Range	T _{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	-	200	°C/W
Thermal Resistance Junction-to-Air *1	R _{θJA}	-	-	368	°C/W

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	60	-	-	V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 60V, V _{GS} = 0V	-	-	0.06	μA
I _{GSS}	Gate-body Leakage	V _{GS} = ±20V, V _{DS} = 0V	-	-	±10	μA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *2	V _{GS} = 10V, I _D = 0.5A	-	1	2.5	Ω
		V _{GS} = 5V, I _D = 0.05A	-	1.1	3	
		V _{GS} = 4.5V, I _D = 0.5A	-	1.2	4	
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.1	1.5	2.4	V
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	26.7	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 20V	-	7.1	-	
C _{RSS}	Reverse Transfer Capacitance	f = 1.0MHz	-	2.2	-	
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time *4	V _{DD} = 30V, I _D = 0.2A V _{GS} = 10V, R _G = 25Ω R _L = 150Ω	-	6	-	ns
t _r	Turn-on Rise Time *4		-	5	-	
t _{d(off)}	Turn-Off Delay Time *4		-	25	-	
t _f	Turn-Off Fall Time *4		-	15	-	
Q _G	Total Gate-Charge	V _{DS} = 10V	-	0.44	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = 4.5V	-	0.14	-	nC
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 0.2A	-	0.2	-	nC
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _S = 0.3A, V _{GS} = 0V	-	0.85	1.2	V

Notes:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 30V, V_{GS} = 10V, L = 0.1mH$
4. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

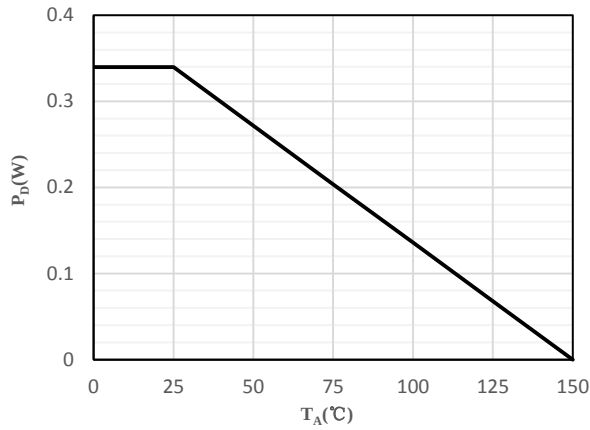


Fig 1 Power Dissipation

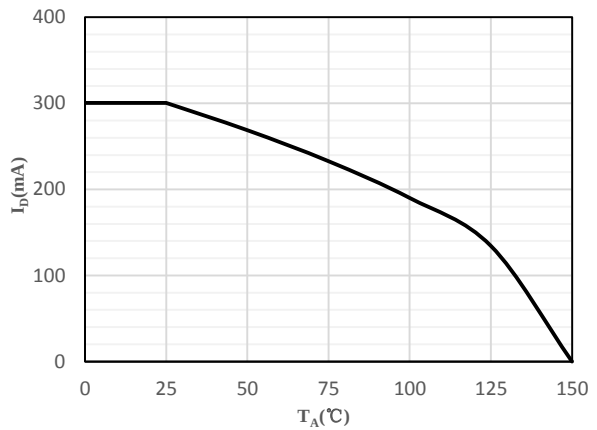


Fig 2 Drain Current

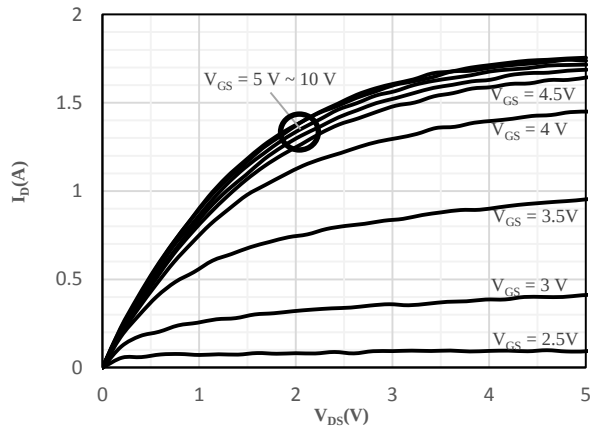


Fig 3 Typical Output Characteristics

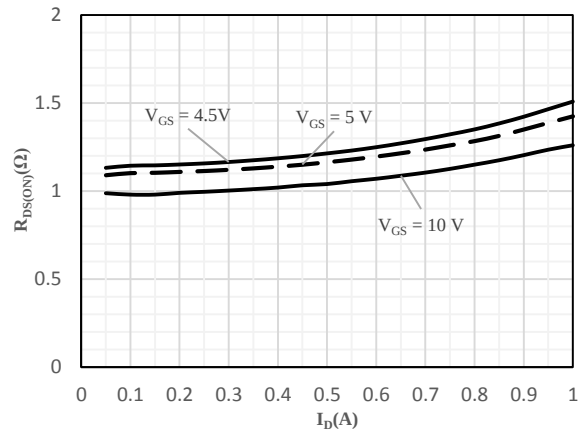


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

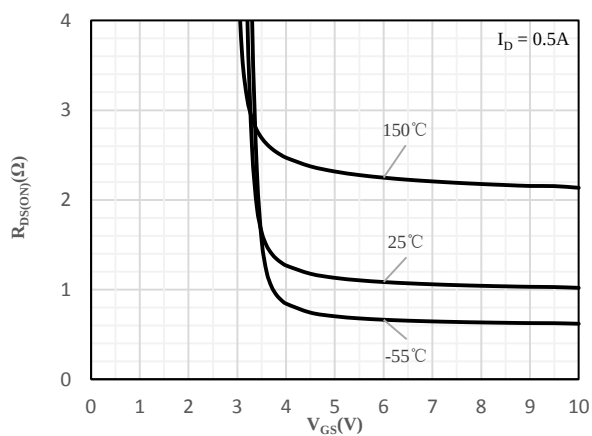


Fig 5 On-Resistance vs. Gate-Source Voltage

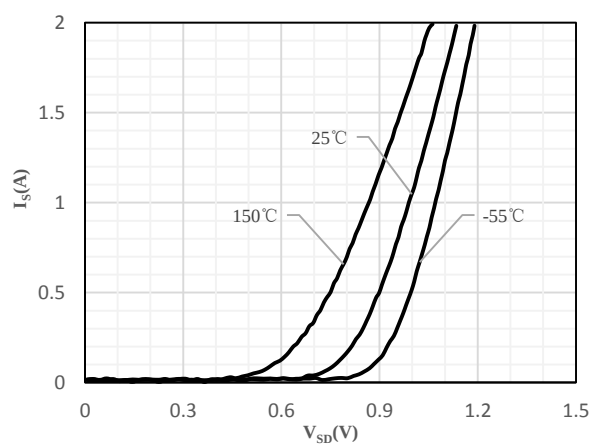


Fig 6 Body-Diode Characteristics

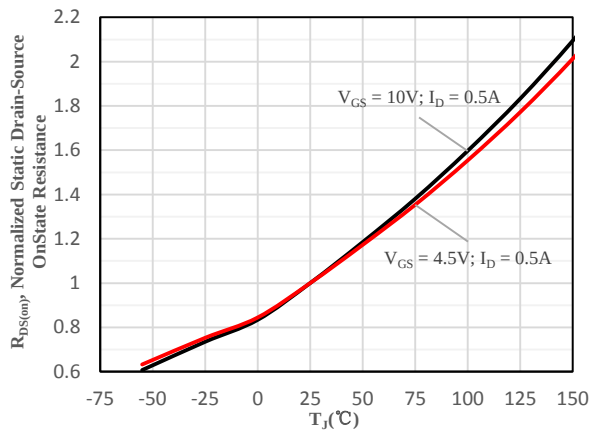


Fig 7 Normalized On-Resistance vs. Junction Temperature

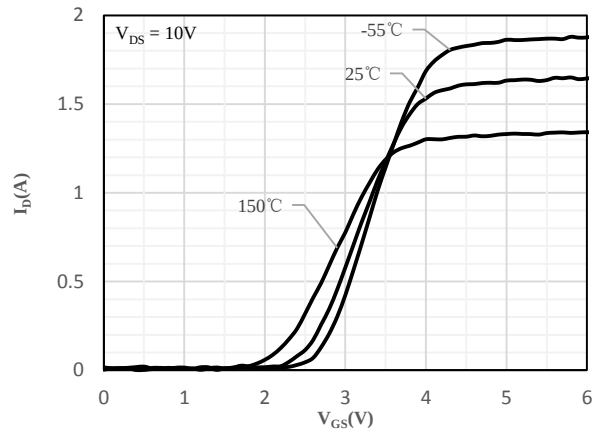


Fig 8 Transfer Characteristics

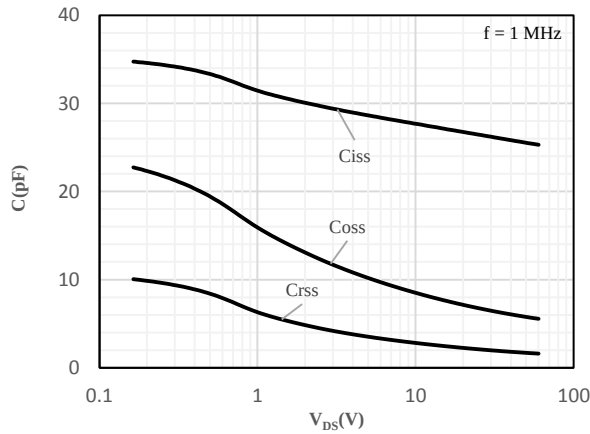


Fig 9 Capacitance Characteristics

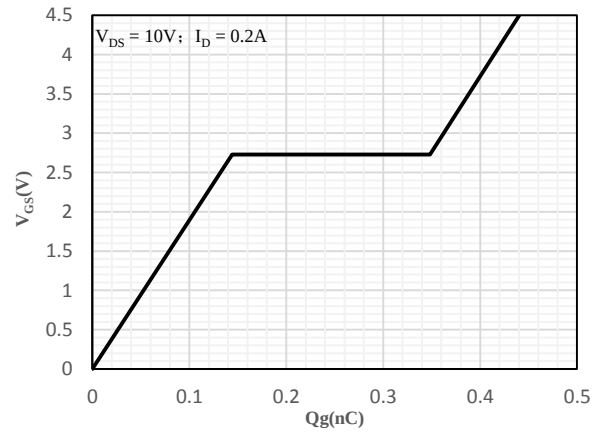


Fig 10 Gate-Charge Characteristics

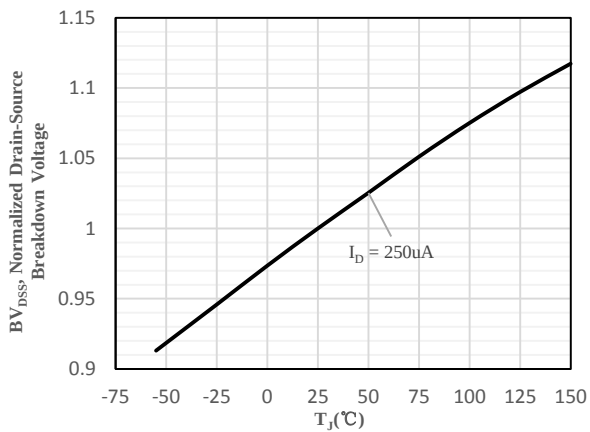


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

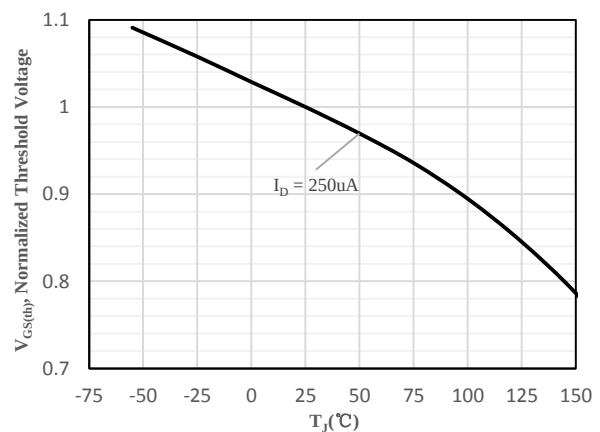
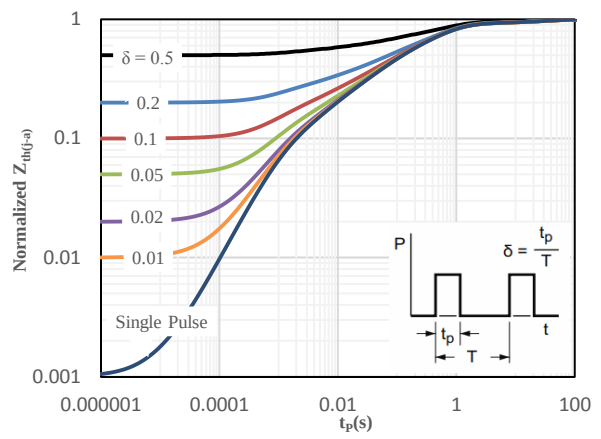
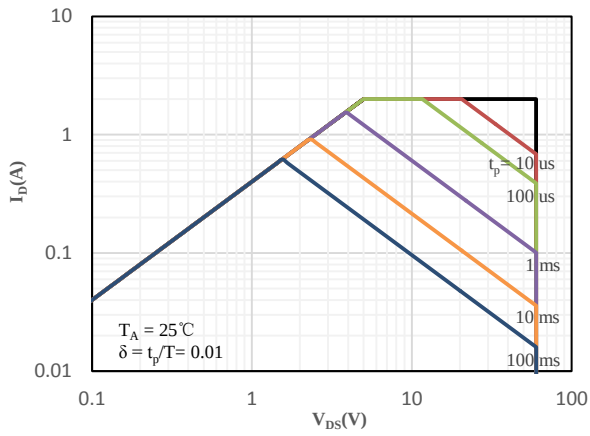
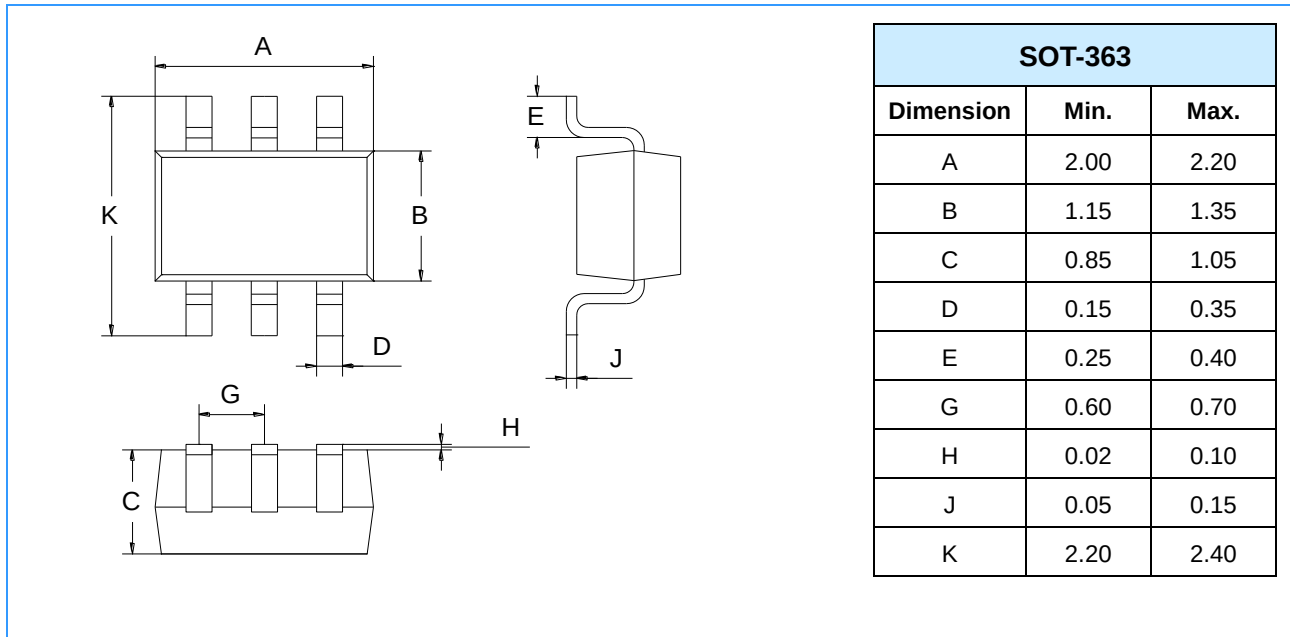


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature



Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)

